



The Rate of Charge Tunneling through Self-Assembled Monolayers Is Insensitive to Many Functional Group Substitutions

Citation

Yoon, Hyo Jae, Nathan D. Shapiro, Kyeng Min Park, Martin M. Thuo, Siowling Soh, and George M. Whitesides. 2012. The Rate of Charge Tunneling through Self-Assembled Monolayers Is Insensitive to Many Functional Group Substitutions. *Angewandte Chemie International Edition* 51, no. 19: 4658–4661.

Published Version

doi:10.1002/anie.201201448

Permanent link

<http://nrs.harvard.edu/urn-3:HUL.InstRepos:11956909>

Terms of Use

This article was downloaded from Harvard University's DASH repository, and is made available under the terms and conditions applicable to Open Access Policy Articles, as set forth at <http://nrs.harvard.edu/urn-3:HUL.InstRepos:dash.current.terms-of-use#OAP>

Share Your Story

The Harvard community has made this article openly available.
Please share how this access benefits you. [Submit a story](#).

[Accessibility](#)

The Rate of Charge Tunneling through Self-Assembled Monolayers is Insensitive to Many Functional Group Substitutions**

Hyo Jae Yoon, Nathan D. Shapiro, Kyeng Min Park, Martin M. Thuo, Siowling Soh, and George M. Whitesides*

At its conception, the field of molecular electronics promised to provide the ability to engineer the rate of charge transport via design of the molecular structure of electronic junctions.^[1] The hypothesis was that the electronic and geometrical structure of molecules in a junction would have a significant and predictable effect on the rate and mechanism of charge transport, through their influence on the energetic topography of the tunneling barrier. Here we show the preparation and electrical characterization of junctions (Figure 1) of the structure $\text{Ag}^{\text{TS}}/\text{S}(\text{CH}_2)_4\text{CONH}(\text{CH}_2)_2\text{R}/\text{Ga}_2\text{O}_3/\text{EGaIn}$ (Ag^{TS} = template-stripped silver surface^[2]; R = tail group; EGaIn = eutectic gallium and indium alloy; Ga_2O_3 = a passivating metal oxide film on the surface of the EGaIn.^[3–5]) including a range of common aliphatic, aromatic, and heteroaromatic organic tail groups. We demonstrate that the rate of charge transport across the self-assembled monolayers (SAMs) is surprisingly insensitive to changes in the structure of the organic molecules of which they are composed. This study is based on a physical-organic design: that is, the information it provides comes from comparisons of rates of tunneling across related structures, rather than from the interpretation of the absolute values of single measurements.

Targets for shaping the tunneling barriers of molecular junctions have included electron-donor-bridge-acceptor molecules^[1a,6], molecular quantum dot systems^[7], aromatic molecules^[8], and complex organic molecules with multiple functional groups.^[9] Many of studies ostensibly shaping the tunneling barriers of molecular junctions have, however, been difficult to interpret, because, when they were carried out, there were no experimental systems that

generated well-characterized, statistically validated data. This paper characterizes the rates of charge transport by tunneling across a series of molecules—arrayed in SAMs—containing a common head group and body ($\text{HS}(\text{CH}_2)_4\text{CONH}(\text{CH}_2)_2-$) and structurally varied tail groups (-R); these molecules are assembled in junctions of the structure $\text{Ag}^{\text{TS}}/\text{SAM}/\text{Ga}_2\text{O}_3/\text{EGaIn}$. Over a range of common aliphatic, aromatic, and heteroaromatic organic tail groups, changing the structure of R does not significantly influence the rate of tunneling. In making these measurements, we utilize **C12** and **C18** alkanethiols as calibration standards to allow comparison with results from other types of junctions.

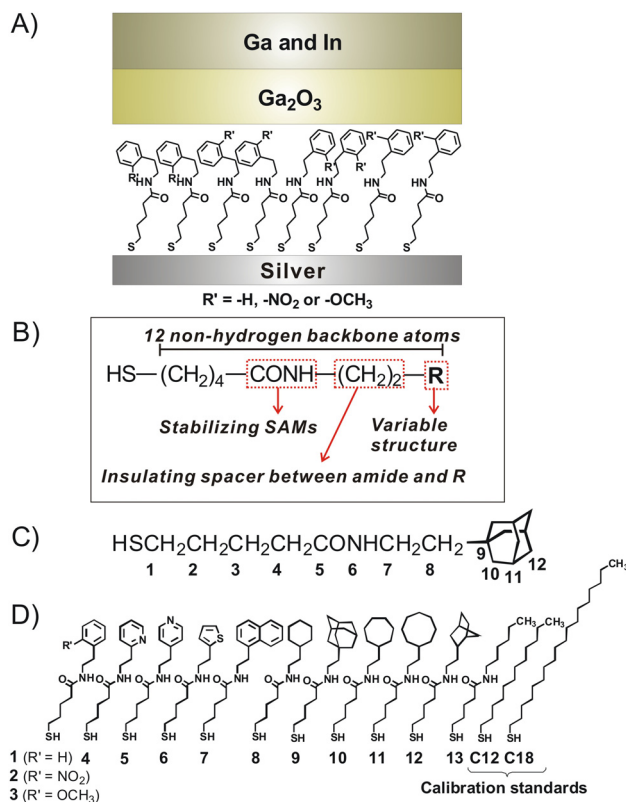


Figure 1. A) Schematic description of tunneling junction consisting of a template-stripped Ag bottom-electrode, supporting a SAM, and contacted by a $\text{Ga}_2\text{O}_3/\text{EGaIn}$ top-electrode. B) A schematic of one junction. C) The numbering system based on non-hydrogen atoms in the backbone of the molecules tested. D) Molecules used to form SAMs.

Limited studies^[4,5,10–15] of charge transport using a range of junctions have described the relation between molecular structure and the rate of tunneling. For example, Venkataraman et al.^[14]

[*] Dr. H. J. Yoon, Dr. N. D. Shapiro, Dr. K. M. Park, Dr. Thuo, M. M., Dr. S. Soh, Prof. G. M. Whitesides
Department of Chemistry and Chemical Biology
Harvard University
12 Oxford Street, Cambridge MA, 02138 USA
E-mail: gwhitesides@gmgroup.harvard.edu

Prof. G. M. Whitesides
Wyss Institute for Biologically Inspired Engineering
Harvard University
60 Oxford Street, Cambridge, MA 02138 USA

Kavli Institute for Bionano Science & Technology
Harvard University
29 Oxford Street, Cambridge MA 02138 USA

[**] This work was supported by a subcontract from Northwestern University from the Department of Energy (DE-SC0000989) for work on synthesis of materials and measurements of charge transport. The NSF Materials Research Science and Engineering Center (DMR-0820484) provided salary support to M.M.T. N.D.S. would like to thank the NIH for a postdoctoral fellowship.



Supporting information for this article is available on the WWW under <http://www.angewandte.org> or from the author.

reported that the rate of charge transport through a series of diaminobenzenes depends on the alignment of the metal Fermi level to the closest molecular orbital. Chiechi and Solomon et al.^[15] compared the rate of charge transport through three different anthracene derivatives of approximately the same thickness, and demonstrated the influence of conjugation on the rate of charge transport. Studies exploring the correlation between molecular structure and charge transport based on systematic physical-organic measurements of the rate of charge transport over a wide range of structures are sparse. This paper describes tunneling rates through SAMs of molecules with a variety of molecular structures including aromatic, heterocyclic, and aliphatic moieties. We have examined ferrocene-terminated SAMs^[4] and SAMs comprising odd- and even-numbered *n*-alkanethiolates.^[5]

Design of the Structure of the SAMs [S(CH₂)₄-CONH-(CH₂)₂R]: Most of the molecules that compose the SAMs in this study were designed to have three features (Figure 1b): i) The total number of non-hydrogen atoms from the sulfur (head) to the most distal point of the tail was 12 (Figure 1c). This constant length allows us to compare values of tunneling currents across these SAMs directly, with no (to a first approximation) corrections for differences in the width of the tunneling barrier. It also gives conveniently measured values of $J(V)$ —the current density, J (A/cm²) across SAMs at non-damaging values of applied potential. ii) The molecules contain a constant amide group (-CONH-); inclusion of this group increases the yield of non-shortng junctions (typically to 85 - 100%) and the stability of the system, relative to junctions prepared from *n*-alkanethiols.^[16] The internal amide also increases the synthetic accessibility of these molecules: the requisite thiols are easily synthesized in synthetic sequences generally comprising only three steps (see Supporting Information). iii) A -CH₂CH₂- unit adjacent to the terminal R group insulates it electronically from the amide.

Choice of Tail Groups (R) in the SAMs: For R, we included: i) aromatic (**1** - **7**) and aliphatic (**8** - **13**) groups; ii) aromatic groups with different structures and patterns of substitution; iii) aliphatic compounds with different degrees of conformational flexibility (**8** - **12**); and iv) groups capable of interacting with the top electrode through donor-acceptor interactions (**2** - **7**).

Ag^{TS}/SAM//Ga₂O₃/EGaIn Junctions: We built molecular junctions with SAMs on ultraflat Ag^{TS} substrates, and liquid-metal (EGaIn) top electrodes by following the procedure for fabrication, reported previously^[3-5] (see Supporting Information for details).

Charge transport is insensitive to many structural changes. Figure 2 summarizes data describing the rate of charge transport through molecules **1** - **13**; Table S1 (in Supporting Information) summarizes information supporting these data. We note four major features: i) Values of $\langle \log |J| \rangle$ are independent of structure within the group **1** - **7**. The values of $J(V=0.5V)$ are not statistically different from that of the **C12** thiol standard. ii) None of the compounds has a rectification ratio greater than 1.4 (Table S1). The small rectification that is observed is likely due to some feature of the junction (for example, differences in work function, or features of the S-Ag and R/Ga₂O₃ interfaces), not to the molecules composing SAMs. iii) The value of $\langle \log |J| \rangle$ for compound **13** is not distinguishable from that of the **C12** thiol although the compounds differ in substitution of a -CONH- group (**13**) for a -CH₂CH₂- group (**C12**). iv) Aliphatic compounds **8** - **13** show slightly lower (by a factor of 4) values of $J(V)$ as the size of the group R increases, perhaps because the thickness of the monolayer increases slightly with bulky groups.

This study varies the structure of the tail group R over a range of structures used typically in organic chemistry, while maintaining an approximately constant thickness to the tunneling barrier. The span of the rates of tunneling current was less than a factor of ~5 over the entire series ($-3.6 \leq \langle \log |J| \rangle \leq -2.9$). This very small response of charge transport to the structure of R suggests that rates of tunneling through SAMs are largely insensitive to differences in the electronic structures of R.

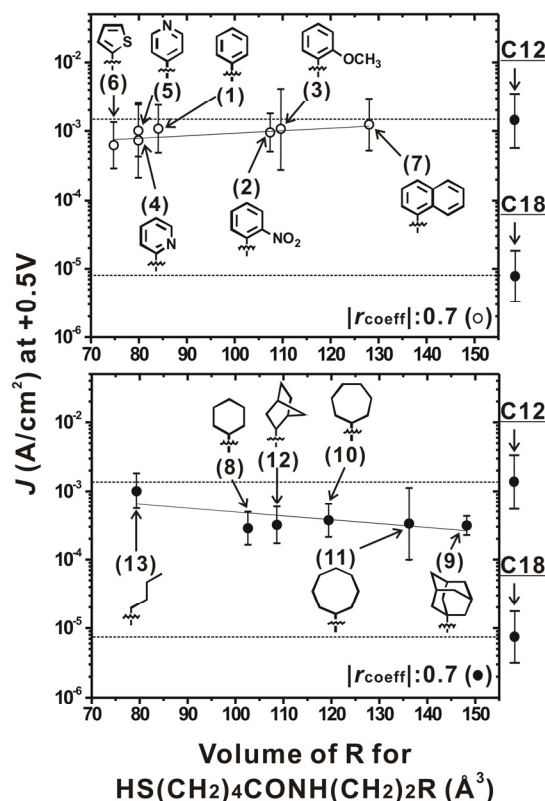


Figure 2. Plots of current densities of amide derivatives **1** - **13** (in Figure 1) and two calibration standard alkanethiols, 1-dodecanethiol (HS-(CH₂)₁₁CH₃, **C12**) and 1-octadecanethiol (HS-(CH₂)₁₇CH₃, **C18**), as a function of volume of the corresponding aromatic and aliphatic tail group (R for HS(CH₂)₄CONH(CH₂)₂R). The dashed lines represent the tunneling current for the calibration standards (**C12** and **C18** alkanethiols), and the solid lines are linear squares fits. The given molecular structures are those of the tail groups, R. The r_{coeff} is a correlation coefficient for each of scatterplot. Molecular volumes of tail groups were calculated from the Molinspiration Property Calculation Service at www.molinspiration.com. (○: Aromatics, ●: Aliphatics)

Casual inspection suggests that the plots of $J(V)$ in Figure 2 show trends: the $J(V)$ for aromatics increases as the volume of R increases, while the $J(V)$ for aliphatics decreases. Statistical analyses, however, indicate that these trends are not statistically significant—more specifically, that the slopes for the linear least square fits are not statistically significantly different from zero at the 95% confidence level (See Supporting Information).

The rates of tunneling across SAMs show a range of responses to their molecular composition, and there is still no single theory that integrates and rationalizes all of these responses. We^[5], Waldeck et al.^[11] and Lee et al.^[12] have previously observed the effect of the interface between metal electrodes and molecules on $J(V)$: an odd-even effect^[5] in SAMs composed of *n*-alkanethiolates,

and the influence of metal–molecule contacts^[11,12] in metal–molecule–metal junctions. Others^[12,15] have reported that conjugation of aromatic units has a large effect on tunneling rates, as do changes in the structure of aromatic groups in the SAM. SAMs composed of ferrocene–terminated *n*-alkanethiolates show significant rectification of current ($r \sim 100$).^[4]

At present it is unclear how to rationalize, for example, the observation of an odd-even effect in *n*-alkanethiolates^[5] with the observation that substitution of R=cyclohexyl by R=phenyl produces only an increase in $J(0.5V)$ of a factor of only ~ 4 (a value which might reflect only a small change in the thickness of the SAM). Indeed, the odd-even effect demonstrates that a small change in molecular structure in the components of a SAM can influence the rate of charge transport across it,^[5] while the change from cyclohexyl to phenyl demonstrates that a large change need not do so. This study does not discount the idea that certain structural changes may change rates of charge transport.^[4,11–13,15] It does suggest that changes in functional groups of the type normally examined in physical–organic chemistry (hydrocarbons, amides, simple aromatics) will be insufficient to produce large changes in $J(V)$ for SAMs of the same thickness.

At the beginning of molecular electronics, it seemed possible that relatively “small” changes to the structure of the SAM (e.g. changes in the dipole moments, aromaticity, polarizability, conductivity of the assembled molecules, or groups in them) would significantly change rates of charge transport by tunneling across them, and result in unusual $J(V)$ characteristics, unusual conductivity, or high rectification. Figure 2 (and Table S1) suggest that, over a range of structures typical of those used in conventional organic chemistry, changing structure, for constant thickness of the SAM, has little influence on rates of tunneling. This conclusion indicates that the rate of charge transport can be modeled by tunneling through a rectangular barrier whose structure at the atomic/molecular level is not important. To summarize this conclusion in slang would be to say “it’s all fat”.

This study has five useful features: i) It improves intuition concerning the types of molecular structures that influence the rate of charge transport across thin, insulating organic films. ii) It outlines a method to improve the accuracy and reliability of measurement of $J(V)$ that intersperses calibration standards among measurements of new compounds. iii) It provides an extensive set of comparable data against which to test theories of charge tunneling in organic matter. iv) It will restrain the enthusiasm of speculation about the range of exotic electronic effects that may be achieved by engineering the structures of organic tunneling barriers. v) It, in combination with other studies,^[4] will suggest directions for research involving functional groups having electronic structures that will, in fact, influence rates of tunneling.

The results described here combine with previous results^[7–9,24,25,27,28] to begin to define the types and energies of orbitals required to influence the shape of tunneling barriers sufficiently to influence the rate of tunneling across them. The results in Figure 2 thus provide an important guide for future research in the field of molecular electronics.

Received: ((will be filled in by the editorial staff))

Published online on ((will be filled in by the editorial staff))

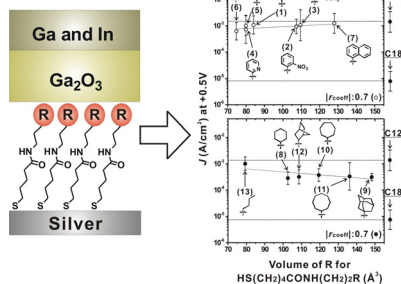
Keywords: charge transport • tunnel junctions • monolayers • EGaIn • molecular electronics

- [1] a) A. Aviram, M. A. Ratner, *Chem. Phys. Lett.* **1974**, *29*, 277–283; b) C. Joachim, J. K. Gimzewski, A. Aviram, *Nature* **2000**, *408*, 541–548; c) A. Nitzan, M. A. Ratner, *Science* **2003**, *300*, 1384–1389; d) N. J. Tao, *Nat. Nanotechnol.* **2006**, *1*, 173–181; d) H. Song, M. A. Reed, T. Lee, *Adv. Mater.* **2011**, *23*, 1583–1608.
- [2] a) E. A. Weiss, R. C. Chiechi, G. K. Kaufman, J. K. Kriebel, Z. Li, M. Duati, M. A. Rampi, G. M. Whitesides, *J. Am. Chem. Soc.* **2007**, *129*, 4336–4349; b) E. A. Weiss, G. K. Kaufman, J. K. Kriebel, Z. Li, R. Schalek, G. M. Whitesides, *Langmuir* **2007**, *23*, 9686–9694.
- [3] Chiechi, R. C.; Weiss, E. A.; Dickey, M. D.; Whitesides, G. M. *Angew. Chem. Int. Ed.* **2008**, *47*, 142–144.
- [4] a) C. A. Nijhuis, W. F. Reus, G. M. Whitesides, *J. Am. Chem. Soc.* **2009**, *131*, 17814–17827; b) C. A. Nijhuis, W. F. Reus, G. M. Whitesides, *J. Am. Chem. Soc.* **2010**, *132*, 18386–18401.
- [5] M. M. Thuo, W. F. Reus, C. A. Nijhuis, J. R. Barber, C. Kim, M. D. Schulz, G. M. Whitesides, *J. Am. Chem. Soc.* **2011**, *133*, 2962–2975.
- [6] a) A. Nitzan, *Annu. Rev. Phys. Chem.* **2001**, *52*, 681–750; b) R. M. Metzger, *Chem. Rev.* **2003**, *103*, 3803–3834.
- [7] a) J. Park, A. N. Pasupathy, J. I. Goldsmith, C. Chang, Y. Yaish, J. R. Petta, M. Rinkoski, J. P. Sethna, H. D. Abruna, P. L. McEuen, D. C. Ralph, *Nature* **2002**, *417*, 722–725; b) W. Liang, M. P. Shores, M. Bockrath, J. R. Long, H. Park, *Nature* **2002**, *417*, 725–729.
- [8] M. A. Reed, C. Zhou, C. J. Muller, T. P. Burgin, J. M. Tour, *Science* **1997**, *278*, 252–254.
- [9] a) W. R. Dichtel, J. R. Heath, J. F. Stoddart, *Philos. Transact. A Math. Phys. Eng. Sci.* **2007**, *365*, 1607–1625; b) J. E. Green, J. W. Choi, A. Boukai, Y. Bunimovich, E. Johnston-Halperin, E. Delonno, Y. Luo, B. A. Sheriff, K. Xu, Y. S. Shin, H. Tseng, J. F. Stoddart, J. R. Heath, *Nature* **2007**, *445*, 414–417.
- [10] a) V. Lemaire, D. A. da Silva Filho, V. Coropceanu, M. Lehmann, Y. Geerts, J. Piris, M. G. Debije, A. M. van de Craats, K. Senthikumar, L. D. Siebbeles, J. M. Warman, J. L. Bredas, J. Cornil, *J. Am. Chem. Soc.* **2004**, *126*, 3271–3279; b) S. Chakrabarti, M. Liu, D. H. Waldeck, A. M. Oliver, M. N. Paddon-Row, *J. Am. Chem. Soc.* **2007**, *129*, 3247–3256; c) F. Wrochem, F. Scholz, A. Schreiber, H. Nothofer, W. E. Ford, P. Morf, T. Jung, A. Yasuda, J. M. Wessels, *Langmuir* **2008**, *24*, 6910–6917; d) G. C. Solomon, D. Q. Andrews, R. H. Goldsmith, T. Hansen, M. R. Wasielewski, R. P. Van Duyne, M. A. Ratner, *J. Am. Chem. Soc.* **2008**, *130*, 17301–17308; e) E. Adaligil, Y. Shon, K. Slowinski, *Langmuir* **2009**, *26*, 1570–1573; f) N. Tuccitto, V. Ferri, M. Cavazzini, S. Quici, G. Zhavnerko, A. Licciardello, M. A. Rampi, *Nat. Mater.* **2009**, *8*, 41–46; g) N. Gergel-Hackett, I. Aguilar, C. A. Richter, *J. Phys. Chem. C* **2010**, *114*, 21708–21714; h) R. K. Hiremath, M. H. Rabinal, B. G. Mulimani, *Phys. Chem. Chem. Phys.* **2010**, *12*, 2564–2568; i) A. B. Ricks, G. C. Solomon, M. T. Colvin, A. M. Scott, K. Chen, M. A. Ratner, M. R. Wasielewski, *J. Am. Chem. Soc.* **2010**, *132*, 15427–15434.
- [11] A. V. Tivanski, Y. He, E. Borguet, H. Liu, G. C. Walker, D. H. Waldeck, *J. Phys. Chem. B* **2005**, *109*, 5398–5402.
- [12] G. Wang, T. Kim, Y. H. Jang, T. Lee, *J. Phys. Chem. C* **2008**, *112*, 13010–13016.
- [13] H. Yan, A. J. Bergren, R. L. McCreery, *J. Am. Chem. Soc.* **2011**, *133*, 19168–19177.
- [14] L. Venkataraman, Y. S. Park, A. C. Whalley, C. Nuckolls, M. S. Hybertsen, M. L. Steigerwald, *Nano. Lett.* **2007**, *7*, 502–506.
- [15] D. Fracasso, H. Valkenier, J. C. Hummelen, G. C. Solomon, R. C. Chiechi, *J. Am. Chem. Soc.* **2011**, *133*, 9556–9563.
- [16] a) R. S. Clegg, J. E. Hutchison, *Langmuir* **1996**, *12*, 5239–5243; b) P. A. Lewis, R. K. Smith, K. F. Kelly, L. A. Bumm, S. M. Reed, R. S. Clegg, J. D. Gunderson, J. E. Hutchison, P. S. Weiss, *J. Phys. Chem. B* **2001**, *105*, 10630–10636.

Self-Assembled Monolayers

Hyo Jae Yoon, Nathan D. Shapiro,
Kyeng Min Park, Martin M. Thuo,
Siowling Soh, and George M.
Whitesides* _____ Page – Page

The Rate of Charge Tunneling through
Self-Assembled Monolayers is
Insensitive to Many Functional Group
Substitutions



This paper characterizes the rates of charge transport by tunneling across a series of molecules—arrayed in self-assembled monolayers—containing a common head group and body (HS(CH₂)₄CONH(CH₂)₂-) and structurally varied tail groups (-R). These molecules are assembled in junctions of the structure Ag^{TS}/SAM//Ga₂O₃/EGaIn. Over a range of common aliphatic, aromatic, and heteroaromatic organic tail groups, changing the structure of R does not significantly influence the rate of tunneling.